

$V_{RRM}$	=	1200	V
$I_F (T_C \leq 135^\circ\text{C})$	=	17.5	A
$Q_C$	=	43	nC

## Silicon Carbide Schottky Diode

### Features

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on  $V_F$
- Temperature-independent Switching
- 175°C Operating Junction Temperature

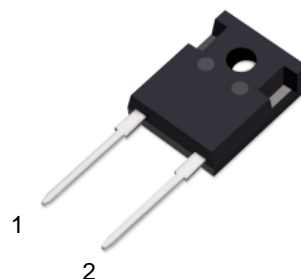
### Benefits

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses

### Applications

- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

### Package



TO-247-2L



Part Number	Package	Marking
THS15C120SK2	TO-247-2L	THS15C120SK2

### Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions	Note
$V_{RRM}$	Repetitive Peak Reverse Voltage	1200	V	$T_C = 25^\circ\text{C}$	
$V_{RSM}$	Surge Peak Reverse Voltage	1200	V	$T_C = 25^\circ\text{C}$	
$V_R$	DC Blocking Voltage	1200	V	$T_C = 25^\circ\text{C}$	
$I_F$	Forward Current	37 17.5 15	A	$T_C \leq 25^\circ\text{C}$ $T_C \leq 135^\circ\text{C}$ $T_C \leq 144^\circ\text{C}$	
$I_{FSM}$	Non-Repetitive Forward Surge Current	135	A	$T_C = 25^\circ\text{C}$ , $t_p = 8.3\text{ms}$ , Half Sine Wave	
$P_{tot}$	Power Dissipation	183	W	$T_C = 25^\circ\text{C}$	Fig.3
$T_C$	Maximum Case Temperature	144	$^\circ\text{C}$		
$T_J, T_{STG}$	Operating Junction and Storage Temperature	-55 to 175	$^\circ\text{C}$		
	TO-247 Mounting Torque	1	Nm	M3 Screw	

## Electrical Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
$V_F$	Forward Voltage	1.55 2.2	1.8 2.5	V	$I_F = 15A, T_J = 25^{\circ}C$ $I_F = 15A, T_J = 175^{\circ}C$	Fig.1
$I_R$	Reverse Current	5 20	20 200	$\mu A$	$V_R = 1200V, T_J = 25^{\circ}C$ $V_R = 1200V, T_J = 175^{\circ}C$	Fig.2
C	Total Capacitance	940 70 57	/	pF	$V_R = 0V, T_J = 25^{\circ}C, f = 1MHz$ $V_R = 400V, T_J = 25^{\circ}C, f = 1MHz$ $V_R = 800V, T_J = 25^{\circ}C, f = 1MHz$	Fig.5
$Q_C$	Total Capacitive Charge	43	/	nC	$V_R = 800V, I_F = 15A$ $di/dt = 200A/\mu s, T_J = 25^{\circ}C$	Fig.4

## Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.82	$^{\circ}C/W$	Fig.6
$R_{\theta JA}$	Thermal Resistance from Junction to Ambient	80	$^{\circ}C/W$	
$T_{sold}$	Soldering Temperature	260	$^{\circ}C$	

## Typical Performance

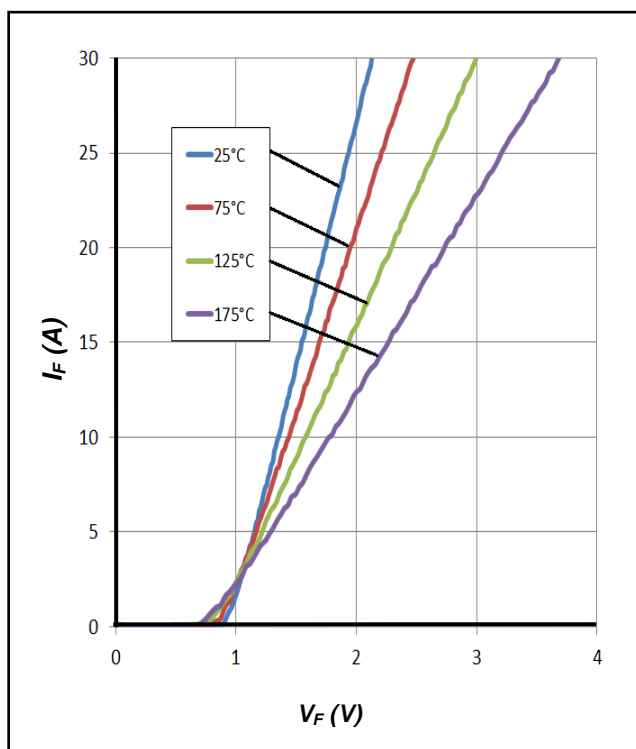


Figure 1. Forward Characteristics

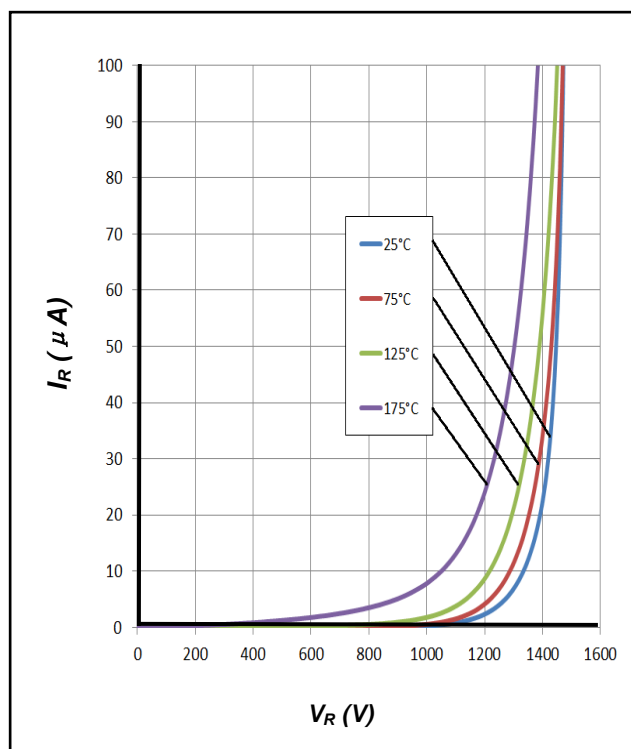


Figure 2. Reverse Characteristics

## Typical Performance

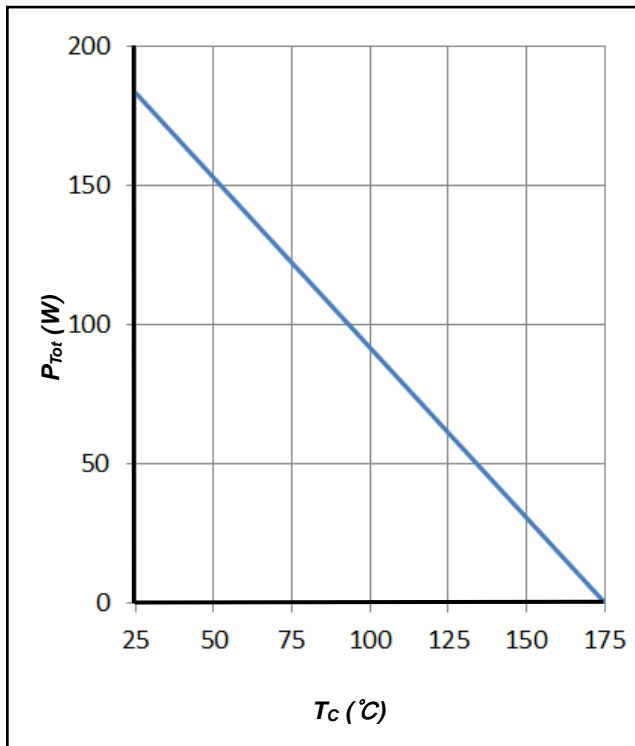


Figure 3. Power Derating

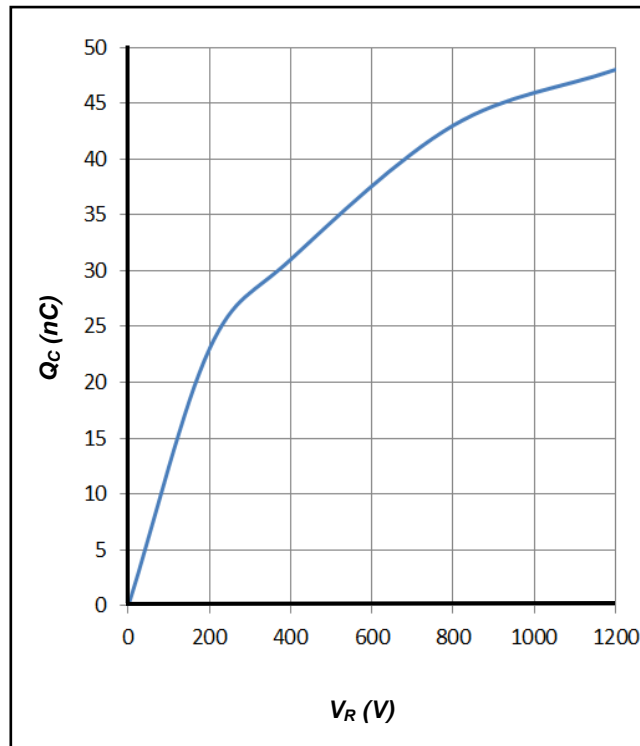


Figure 4. Total Capacitive Charge vs. Reverse Voltage

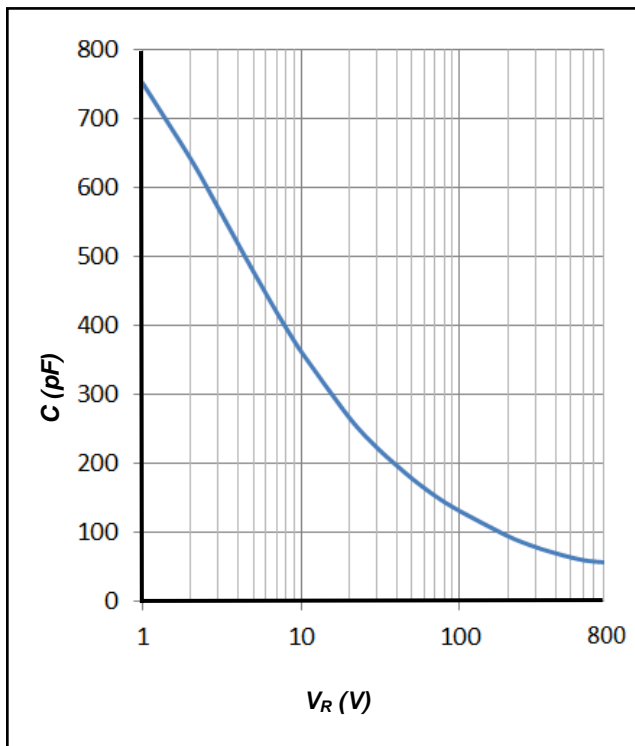


Figure 5. Total Capacitance vs. Reverse Voltage

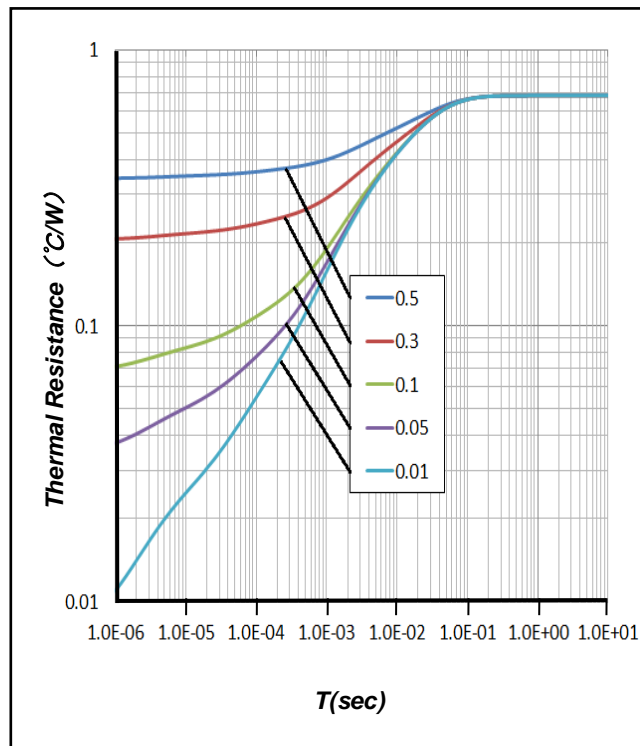
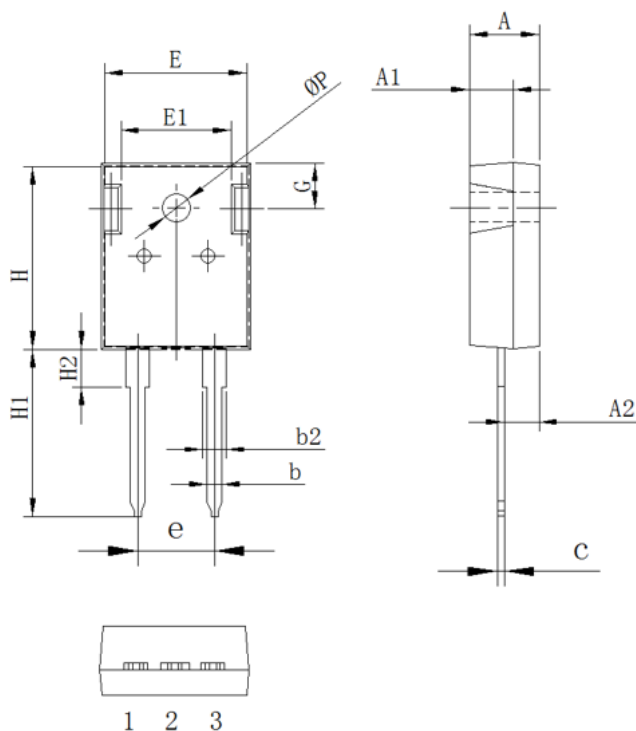


Figure 6. Transient Thermal Impedance

## Package Information

### TO-247-2L PACKAGE



symbol	单位mm		
	Min	Nom	Max
A	4.8	5.00	5.20
A1	3.3	3.5	3.7
A2	2.20	2.40	2.60
b	1.00	1.2	1.40
b1	2.90	3.10	3.30
b2	1.90	2.10	2.30
c	0.50	0.60	0.70
e	10.5	10.9	11.3
E	15.2	15.7	16.2
E1	10.2	10.7	11.2
H	20.8	21	21.2
H1	19.5	20.0	20.5
H2	4.00	4.20	4.40
G	5.60	5.80	600
P	3.50	3.70	3.90

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